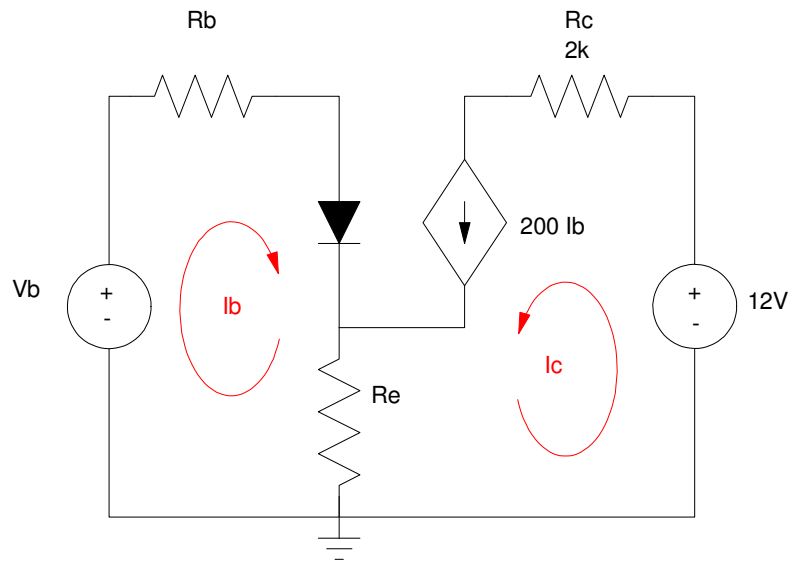
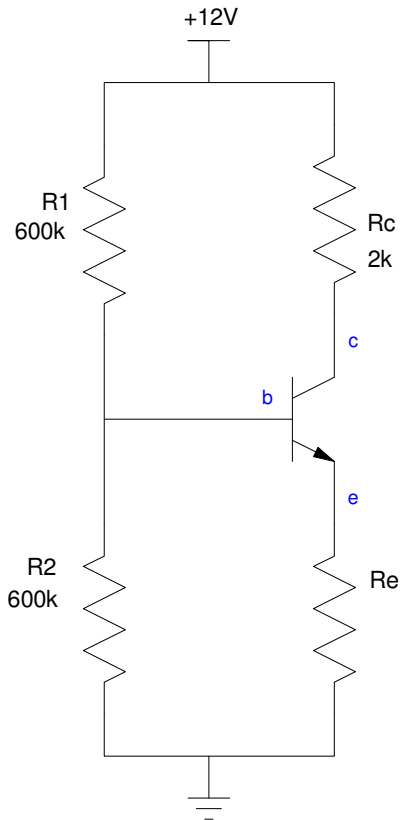


ECE 321 - Quiz #4 - Name _____

BJT Amplifiers. Spring 2023

1) BJT Amplifier: DC Analysis. Determine the Thevenin equivalent of R1 and R2 as well as the Q-point. Assume ideal silicon transistors:

- $V_{be} = 0.7V$
- $\beta = 200$
- $R_e = 800 + 100 * (\text{your birth month}) + (\text{your birth day})$.



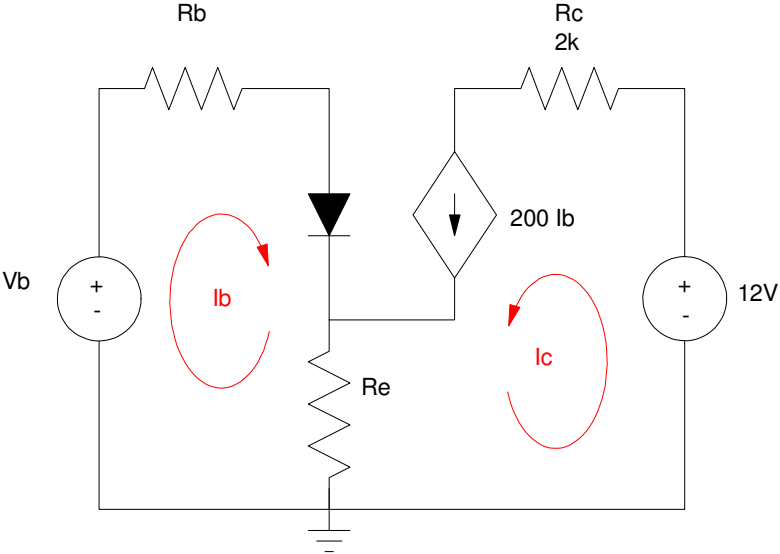
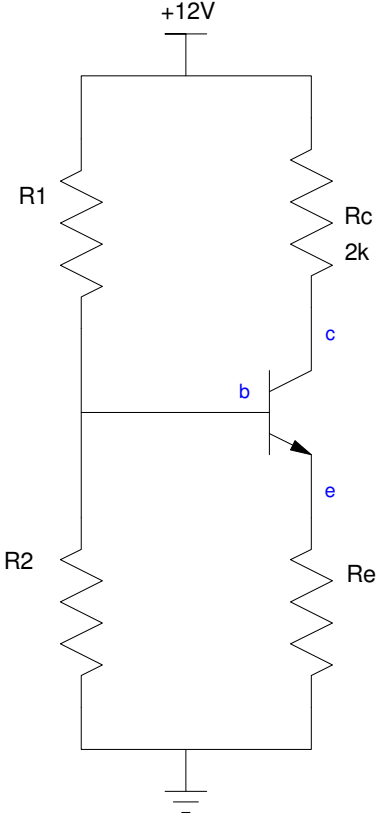
R_e $800 + 100 * mo + day$	V_b	R_b	V_{ce}	I_c

2) BJT Amplifier: DC Design. Determine R1 and R2 so that

- The Q point is $V_c = 8.00V$ and
- The Q point is stabilized for variations in β

Assume

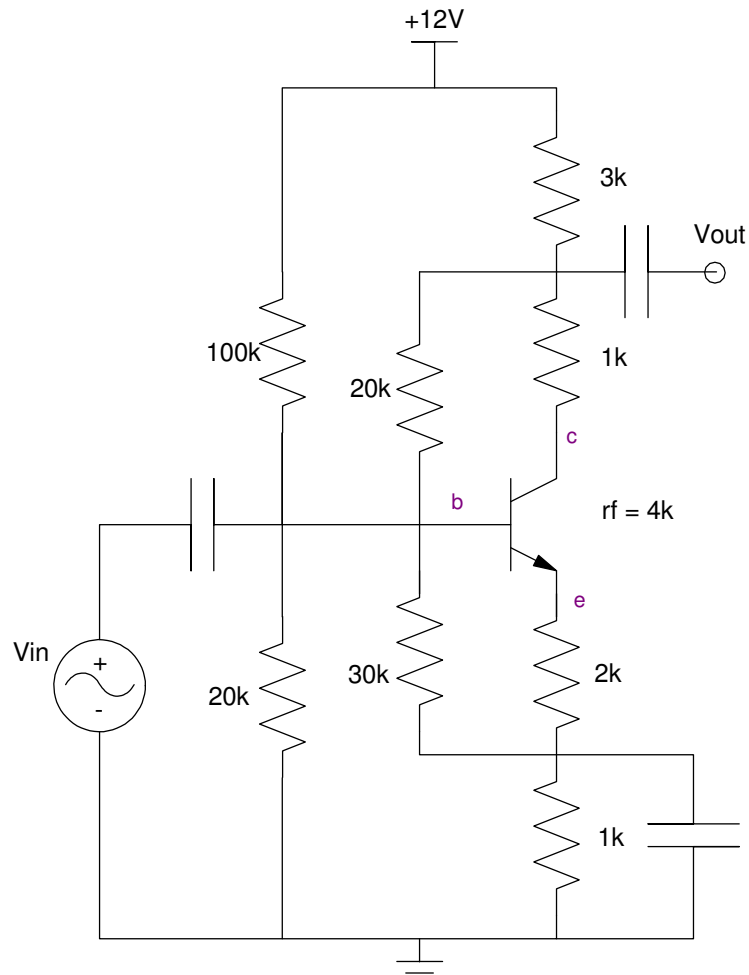
- Ideal silicon transistors ($V_{be} = 0.7V, \beta = 200$)
- $R_e = 800 + 100*(\text{birth month}) + (\text{birth day})$.



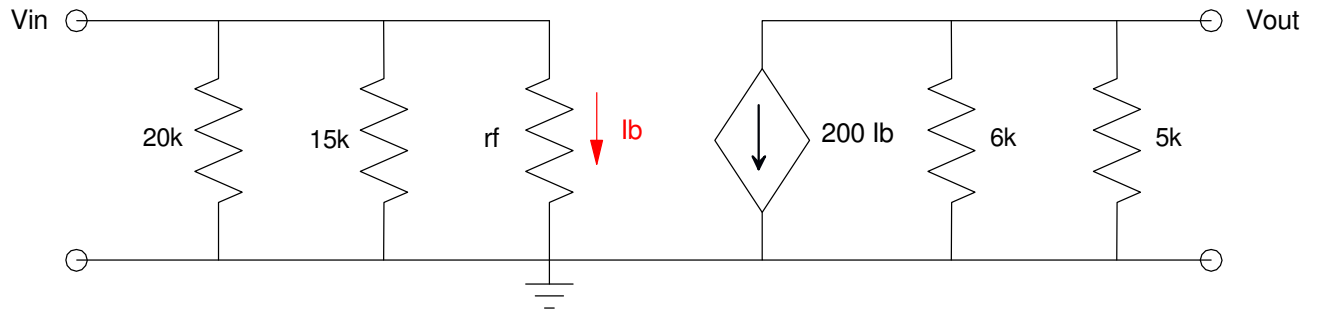
R_e $800 + 100*mo + day$	R_1	R_2	V_b	R_b

3) BJT: AC Analysis: Draw the small signal model for the following BJT amplifier. Assume

- $r_f = 4k\Omega$
- $\beta = 200$



4) BJT: AC Analysis: Determine the 2-port model for the following CE amplifier.



r_f	R_{in}	A_{in}	R_{out}	A_o
$800 + 100 \cdot m_o + day$				

5) 2-Port model (experimental): Determine the 2-port parameters based upon the following experimental data:

Case 1:

- $V_{in} = 1\text{mV @ } 1\text{kHz}$
- $R_1 = 0\text{ Ohms}$
- $R_2 = 10\text{M Ohms}$

results in $V_{out} = 230\text{V}$

Case 2:

- $V_{in} = 1\text{mV @ } 1\text{kHz}$
- $R_1 = X\text{ Ohms}$
- $R_2 = 10\text{M Ohms}$

results in $V_{out} = 170\text{mV}$

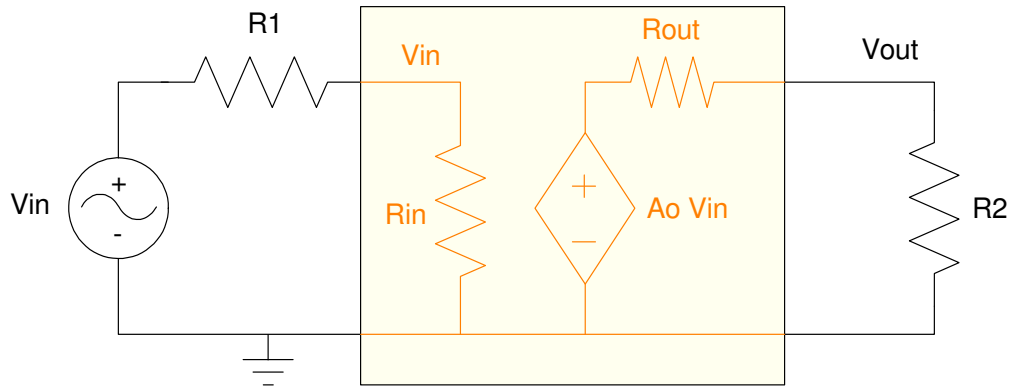
Case 3

- $V_{in} = 1\text{mV @ } 1\text{kHz}$
- $R_1 = 0\text{ Ohms}$
- $R_2 = X\text{ Ohms}$

results in $V_{out} = 130\text{mV}$

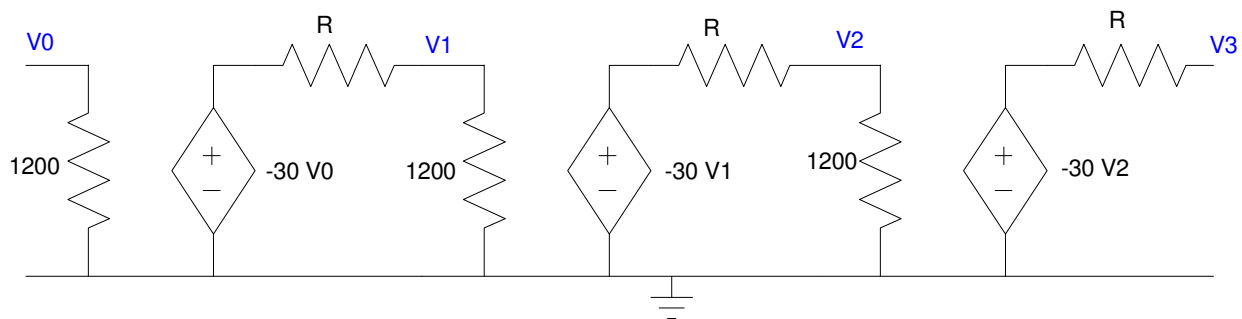
Assume

- $X = 800 + 100 * (\text{your birth month}) + (\text{your birth date})\text{ Ohms}$



X $800 + 100 * mo + day$	R_{in}	A_i	R_{out}	A_o
		0		

6) Determine the 2-port model for the following cascaded CE amplifier



R $800 + 100 \cdot \text{mo} + \text{day}$	R_{in}	A_i	R_{out}	A_o